



PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) J.O. Chu, et al.

Examiner: Savitri Mulpuri

Serial No.: 09/838,892

Art Unit: 1665

Filed: April 20, 2003

Docket: YOR920010308US1 (16315)

For: EPITAXIAL AND POLYCRYSTALLINE
GROWTH OF $Si_{1-x-y}Ge_xC_y$ AND $Si_{1-y}C_y$
ALLOY LAYERS ON Si By UHV-CVD

Dated: March 12, 2003

Commissioner for Patents
Washington, DC 20231

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AMENDMENT AND RESPONSE

Sir:

In response to the Office Action dated December 12, 2002, applicants submit the following amendments and remarks for entry of record in the above-identified patent application.

IN THE CLAIMS:

Please cancel Claims 4, 6, 17 and 18, without prejudice or disclaimer, and please amend

Claims 1, 12, 13, 14, 27 and 28 to read as follows:

1. (Amended) A method for forming an alloy layer of silicon carbon on a

G1

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231 on March 12, 2003.

Dated: March 12, 2003

Janet Grossman
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